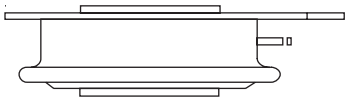
Inverter Grade Thyristors (Hockey PUK Version), 370 A



TO-200AB (A-PUK)

FEATURES

- Metal case with ceramic insulator
- All diffused design
- Center amplifying gate
- International standard case TO-200AB (A-PUK)
- Guaranteed high dV/dt
- Guaranteed high dI/dt
- High surge current capability
- Low thermal impedance
- High speed performance

Pb-free
RoHS COMPLIANT

PRODUCT SUMMARY	
$I_{T(AV)}$	370 A

TYPICAL APPLICATIONS

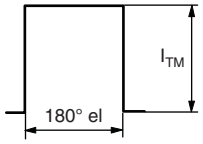
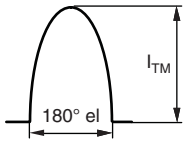
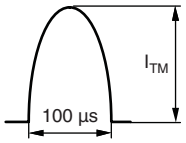
- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		370	A
	T_{hs}	55	°C
$I_{T(RMS)}$		690	A
	T_{hs}	25	°C
I_{TSM}	50 Hz	4900	A
	60 Hz	5130	
I^2t	50 Hz	120	kA^2s
	60 Hz	110	
V_{DRM}/V_{RRM}		400 to 800	V
t_q	Range	10 to 20	µs
T_J		- 40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM}, MAXIMUM REPETITIVE PEAK VOLTAGE V	V_{RSM}, MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
ST183C..C	04	400	500	40
	08	800	900	

CURRENT CARRYING CAPABILITY

FREQUENCY							UNITS
50 Hz	770	660	1220	1160	5450	4960	A
400 Hz	730	600	1270	1090	2760	2420	
1000 Hz	600	490	1210	1040	1600	1370	
2500 Hz	350	270	860	730	800	680	
Recovery voltage V_r	50		50		50		V
Voltage before turn-on V_d	V_{DRM}		V_{DRM}		V_{DRM}		
Rise of on-state current dI/dt	50		-		-		A/µs
Heatsink temperature	40	55	40	55	40	55	°C
Equivalent values for RC circuit	47/0.22		47/0.22		47/0.22		Ω/µF

ON-STATE CONDUCTION

PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at heatsink temperature	$I_{T(AV)}$	180° conduction, half sine wave double side (single side) cooled			370 (130)	A
					55 (85)	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 25 °C heatsink temperature double side cooled			690	A
Maximum peak, one half cycle, non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	4900	
		t = 8.3 ms			5130	
		t = 10 ms	100 % V_{RRM} reapplied		4120	
		t = 8.3 ms			4310	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied		120	kA^2s
		t = 8.3 ms			110	
		t = 10 ms	100 % V_{RRM} reapplied		85	
		t = 8.3 ms			78	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied			1200	$kA^2\sqrt{s}$
Maximum peak on-state voltage	V_{TM}	I_{TM} = 600 A, $T_J = T_J$ maximum, t_p = 10 ms sine wave pulse			1.80	V
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			1.40	
High level value of threshold voltage	$V_{T(TO)2}$	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			1.45	
Low level value of forward slope resistance	r_{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.67	mΩ
High level value of forward slope resistance	r_{t2}	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.58	
Maximum holding current	I_H	T_J = 25 °C, I_T > 30 A			600	mA
Typical latching current	I_L	T_J = 25 °C, V_A = 12 V, R_a = 6 Ω, I_G = 1 A			1000	

SWITCHING					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned on current		dI/dt	$T_J = T_J$ maximum, V_{DRM} = Rated V_{DRM} I_{TM} = 2 x dI/dt	1000	A/µs
Typical delay time		t_d	T_J = 25 °C, V_{DM} = Rated V_{DRM}, I_{TM} = 50 A DC, t_p = 1 µs Resistive load, gate pulse: 10 V, 5 Ω source	1.1	µs
Maximum turn-off time	minimum	t_q	$T_J = T_J$ maximum, I_{TM} = 300 A, commutating dI/dt = 20 A/µs V_R = 50 V, t_p = 500 µs, dV/dt: See table in device code	10	
	maximum			20	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % V_{DRM}, higher value available on request	500	V/µs
Maximum peak reverse and off-state leakage current	I_{RRM}, I_{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	40	mA

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, f = 50 Hz, d% = 50	60	W
Maximum average gate power	$P_{G(AV)}$		10	
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms	10	A
Maximum peak positive gate voltage	+ V_{GM}		20	V
Maximum peak negative gate voltage	- V_{GM}		5	
Maximum DC gate currrent required to trigger	I_{GT}	T_J = 25 °C, V_A = 12 V, R_a = 6 Ω	200	mA
Maximum DC gate voltage required to trigger	V_{GT}		3	V
Maximum DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum, rated V_{DRM} applied	20	mA
Maximum DC gate voltage not to trigger	V_{GD}		0.25	V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	T_J		- 40 to 125	°C
Maximum storage temperature range	T_{Stg}		- 40 to 150	
Maximum thermal resistance, junction to heatsink	$R_{thJ\text{-}hs}$	DC operation single side cooled	0.17	K/W
		DC operation double side cooled	0.08	
Maximum thermal resistance, case to heatsink	$R_{thC\text{-}hs}$	DC operation single side cooled	0.033	
		DC operation double side cooled	0.017	
Mounting force, ± 10 %			4900 (500)	N (kg)
Approximate weight			50	g
Case style		See dimensions - link at the end of datasheet	TO-200AB (A-PUK)	

$\Delta R_{thJ\text{-}hs}$ CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.015	0.016	0.011	0.011	$T_J = T_J$ maximum	K/W
120°	0.018	0.019	0.019	0.019		
90°	0.024	0.024	0.026	0.026		
60°	0.035	0.035	0.036	0.037		
30°	0.060	0.060	0.060	0.061		

Note

- The table above shows the increment of thermal resistance $R_{thJ\text{-}hs}$ when devices operate at different conduction angles than DC

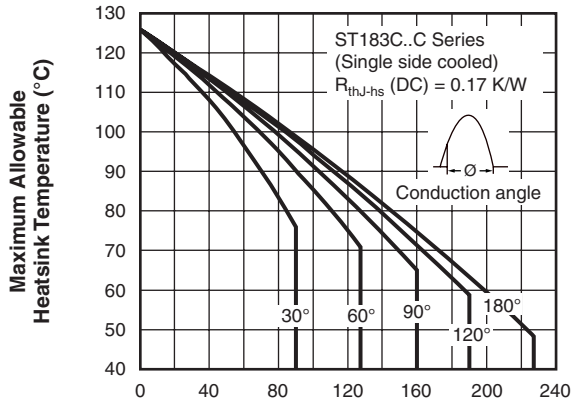


Fig. 1 - Current Ratings Characteristics

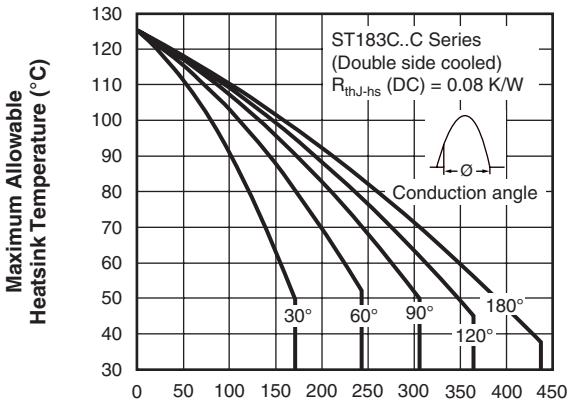


Fig. 3 - Current Ratings Characteristics

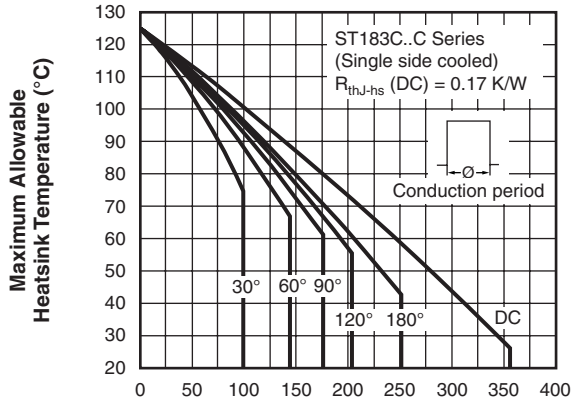


Fig. 2 - Current Ratings Characteristics

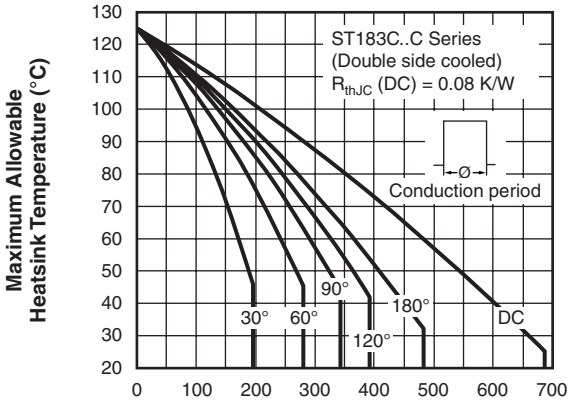


Fig. 4 - Current Ratings Characteristics

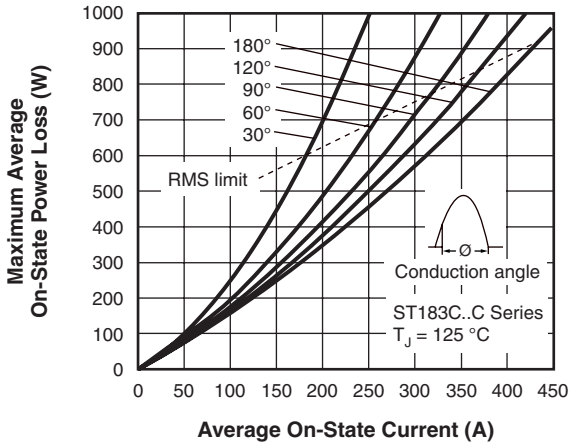


Fig. 5 - On-State Power Loss Characteristics

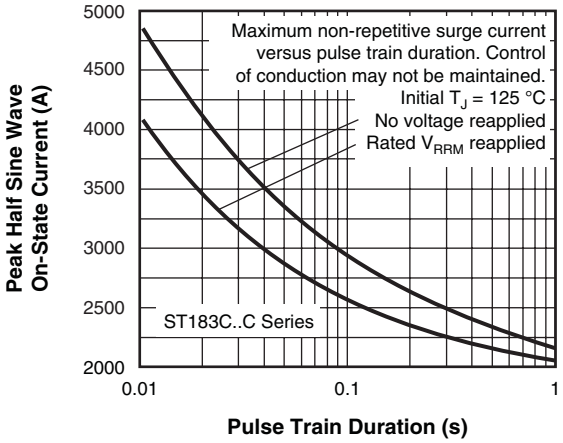


Fig. 8 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

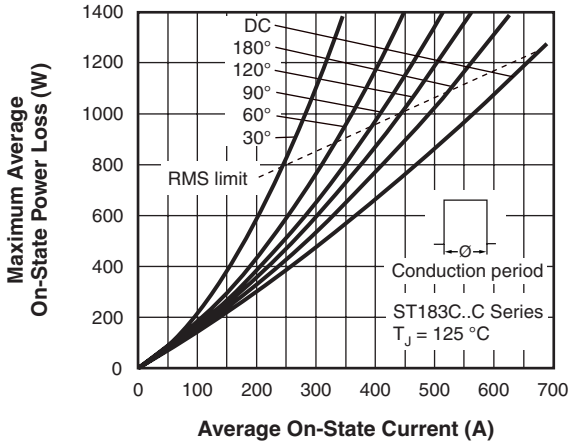


Fig. 6 - On-State Power Loss Characteristics

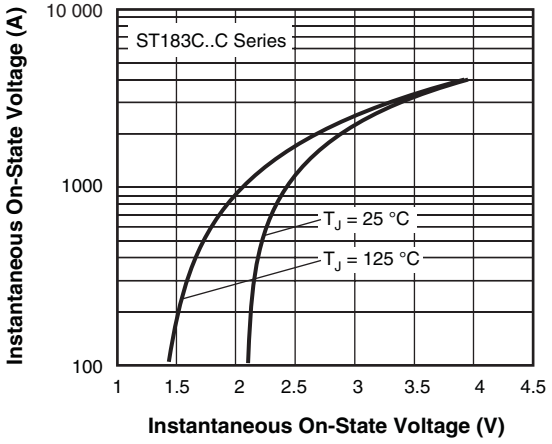


Fig. 9 - On-State Voltage Drop Characteristics

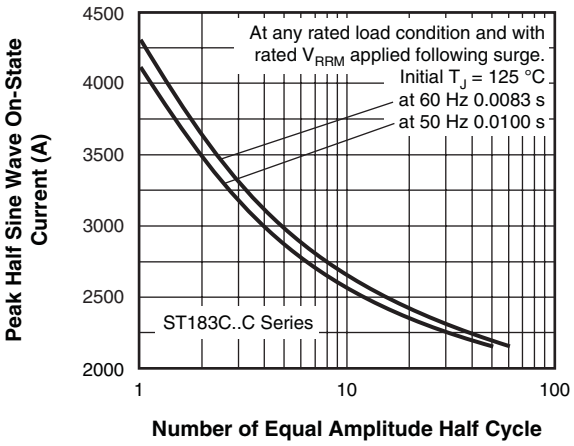


Fig. 7 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

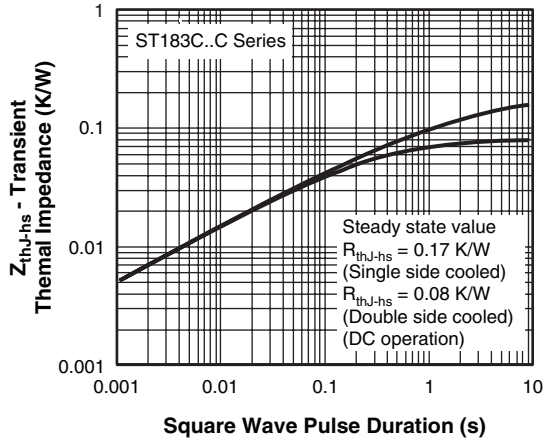


Fig. 10 - Thermal Impedance Z_{thJC} Characteristics

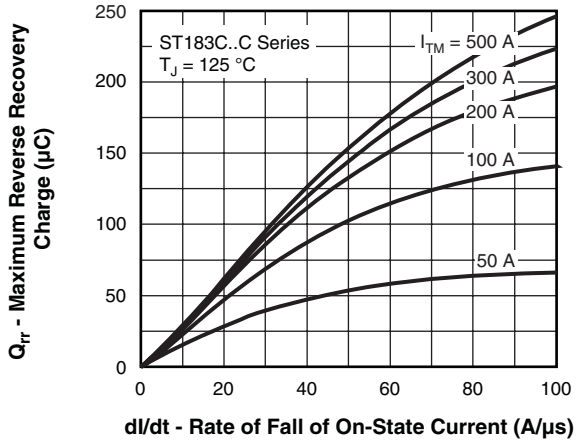


Fig. 11 - Reverse Recovered Charge Characteristics

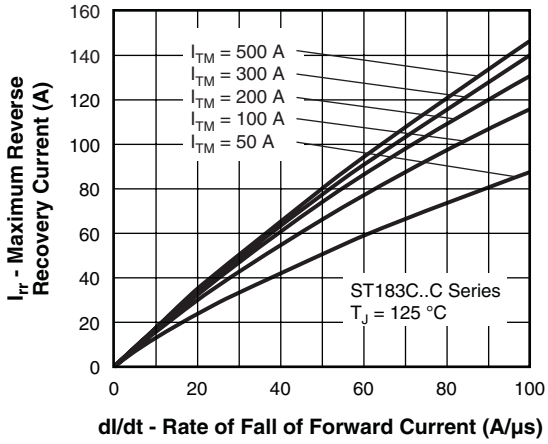


Fig. 12 - Reverse Recovery Current Characteristics

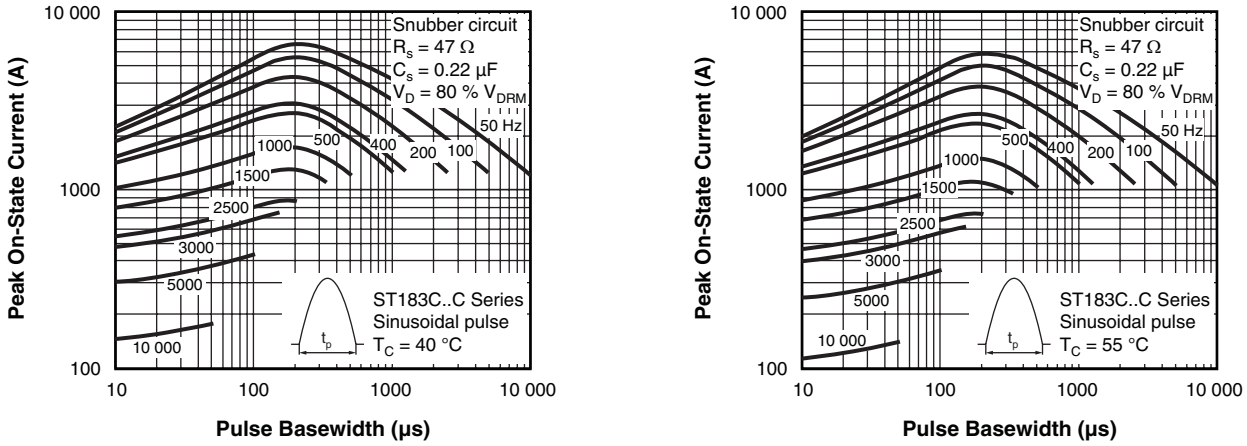


Fig. 13 - Frequency Characteristics

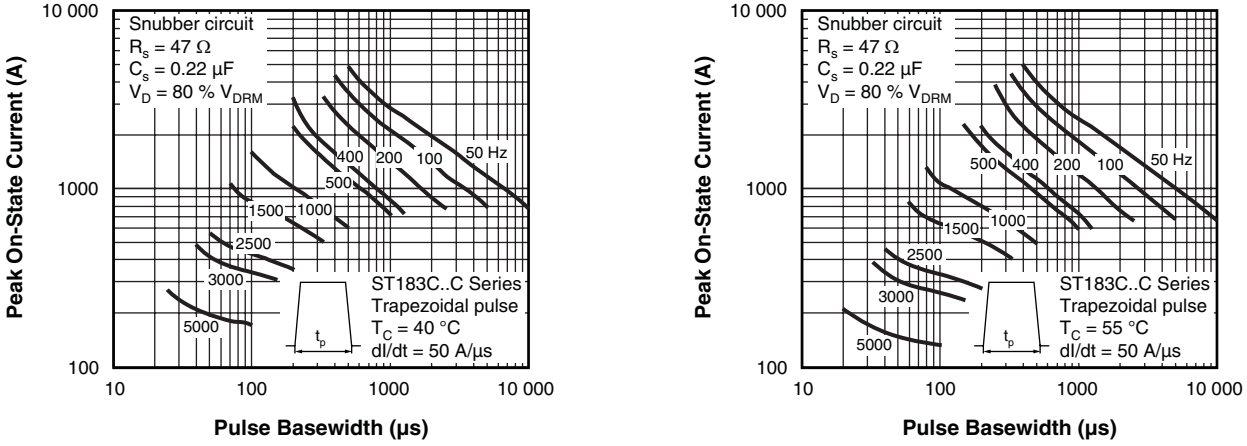


Fig. 14 - Frequency Characteristics

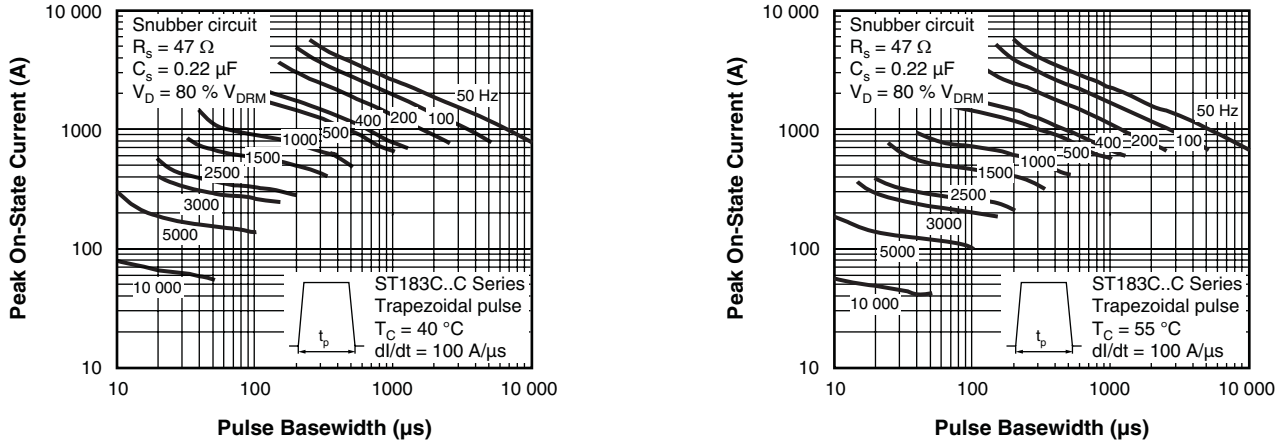


Fig. 15 - Frequency Characteristics

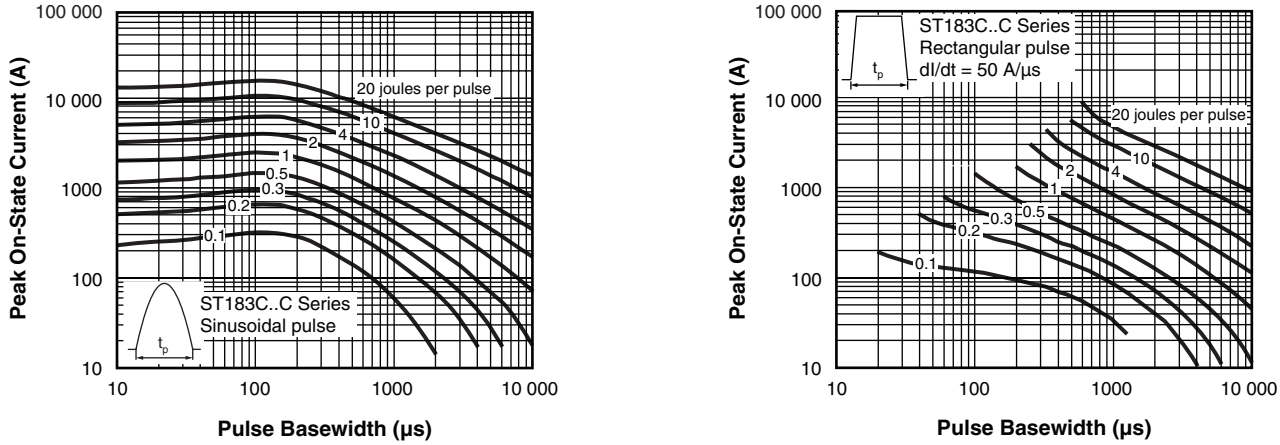


Fig. 16 - Maximum On-State Energy Power Loss Characteristics

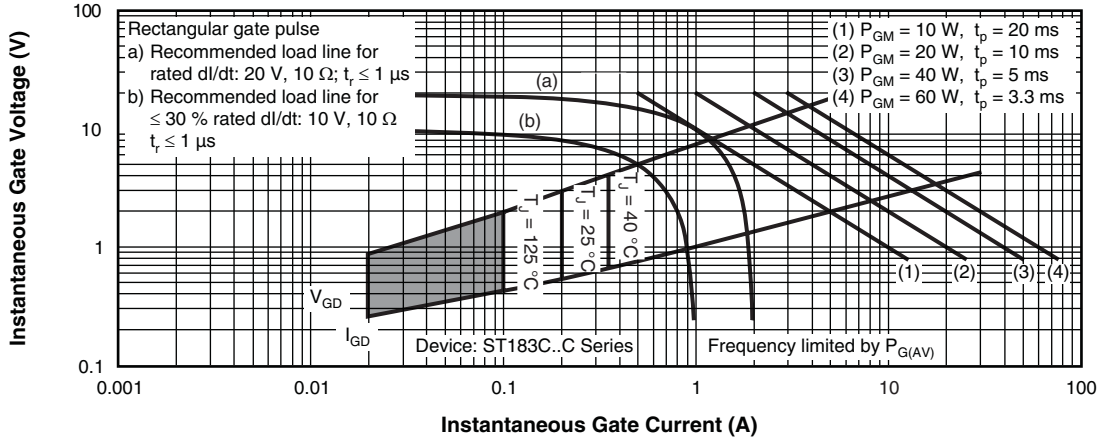


Fig. 17 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code

ST	18	3	C	08	C	H	K	-	1	P
1	2	3	4	5	6	7	8	9	10	11

- **1** - Thyristor
- **2** - Essential part number
- **3** - 3 = Fast turn-off
- **4** - C = Ceramic PUK
- **5** - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- **6** - C = PUK case TO-200AB (A-PUK)
- **7** - Reapplied dV/dt code (for t_q test condition)
- **8** - t_q code
- **9** - 0 = Eyelet terminals
  (gate and aux. cathode unsoldered leads)
  1 = Fast-on terminals
  (gate and aux. cathode unsoldered leads)
  2 = Eyelet terminals
  (gate and aux. cathode soldered leads)
  3 = Fast-on terminals
  (gate and aux. cathode soldered leads)
- **10** - Critical dV/dt:
  - None = 500 V/µs (standard value)
  - L = 1000 V/µs (special selection)
- **11** - P = Lead (Pb)-free

dV/dt - t_q combinations available

t_q (µs) \ dV/dt (V/µs)	20	50	100	**200**	400
10	CN	DN	EN	**FN***	HN
12	CM	DM	EM	FM	HM
15	CL	DL	EL	**FL***	HL
18	CP	DP	EP	FP	HP
20	CK	DK	EK	FK	HK

* Standard part number.
All other types available only on request.

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95074

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